

INCH-POUND

The documentation and process conversion measures necessary to comply with this document shall be completed by 4 September 2019.

MIL-PRF-19500/534J  
 4 June 2019  
 SUPERSEDING  
 MIL-PRF-19500/534H  
 14 November 2014

PERFORMANCE SPECIFICATION SHEET

TRANSISTOR, NPN, SILICON, POWER, TYPES 2N5002 AND 2N5004,  
 ENCAPSULATED (CASE MOUNT PACKAGE) AND UNENCAPSULATED, RADIATION HARDNESS ASSURANCE,  
 QUALITY LEVELS JAN, JANTX, JANTXV, JANS, JANHC AND JANKC

This specification is approved for use by all Departments  
 and Agencies of the Department of Defense.

The requirements for acquiring the product described herein shall consist of  
 this specification sheet and [MIL-PRF-19500](#).

1. SCOPE

1.1 Scope. This specification covers the performance requirements for NPN, silicon, power transistors for use in high-speed power-switching applications. Four levels of product assurance (JAN, JANTX, JANTXV, and JANS) are provided for each encapsulated device type as specified in [MIL-PRF-19500](#). Two levels of product assurance (JANHC and JANKC) for each unencapsulated device type die.

1.2 Physical dimensions.

1.2.1 Package outlines. The device package outline is a TO-210AA (formerly TO-59) in accordance with [figure 1](#) for all encapsulated device types.

1.2.2 Unencapsulated die. The dimensions and topography for JANHC and JANKC unencapsulated die are in accordance with [figure 2](#).

1.3 Maximum ratings. Unless otherwise specified  $T_A = +25^\circ\text{C}$ .

$P_T$ (1) $T_A = 25^\circ\text{C}$	$P_T$ (2) $T_C = 25^\circ\text{C}$	$R_{\theta JA}$	$R_{\theta JC}$ (3)	$V_{CBO}$	$V_{CEO}$	$V_{EBO}$	$I_C$	$I_C$ (4)	Reverse pulse energy (5)	$T_{stg}$ and $T_J$
<u>W</u>	<u>W</u>	<u><math>^\circ\text{C/W}</math></u>	<u><math>^\circ\text{C/W}</math></u>	<u>V dc</u>	<u>V dc</u>	<u>V dc</u>	<u>A dc</u>	<u>A dc</u>	<u>mJ</u>	<u><math>^\circ\text{C}</math></u>
2	58	88	3	100	80	5.5	5	10	15	-65 to +200

- (1) Derate linearly 11.4 mW/ $^\circ\text{C}$  for  $T_A > 25^\circ\text{C}$ .
- (2) For derating see [figure 3](#).
- (3) For thermal impedance see [figure 4](#).
- (4) This value applies for  $P_w \leq 8.3$  ms, duty cycle  $\leq 1$  percent.
- (5) This rating is based on the capability of the transistors to operate safely in the unclamped inductive load energy test circuit [figure 5](#) herein.

Comments, suggestions, or questions on this document should be addressed to DLA Land and Maritime, ATTN: VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to [Semiconductor@dla.mil](mailto:Semiconductor@dla.mil). Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at <https://assist.dla.mil>.

AMSC N/A

